

Silicon NPN Power Transistors

2SC2305

DESCRIPTION

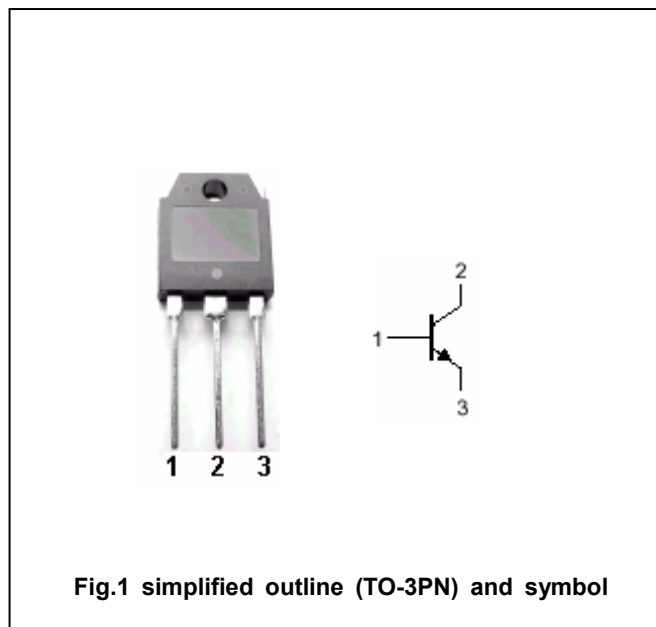
- With TO-3PN package
- High breakdown voltage
- Fast switching speed
- Wide safe operating area

APPLICATIONS

- For switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	400	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	8	V
I_C	Collector current (DC)		7	A
I_{CM}	Collector current-peak		14	A
I_B	Base current (DC)		3	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	80	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

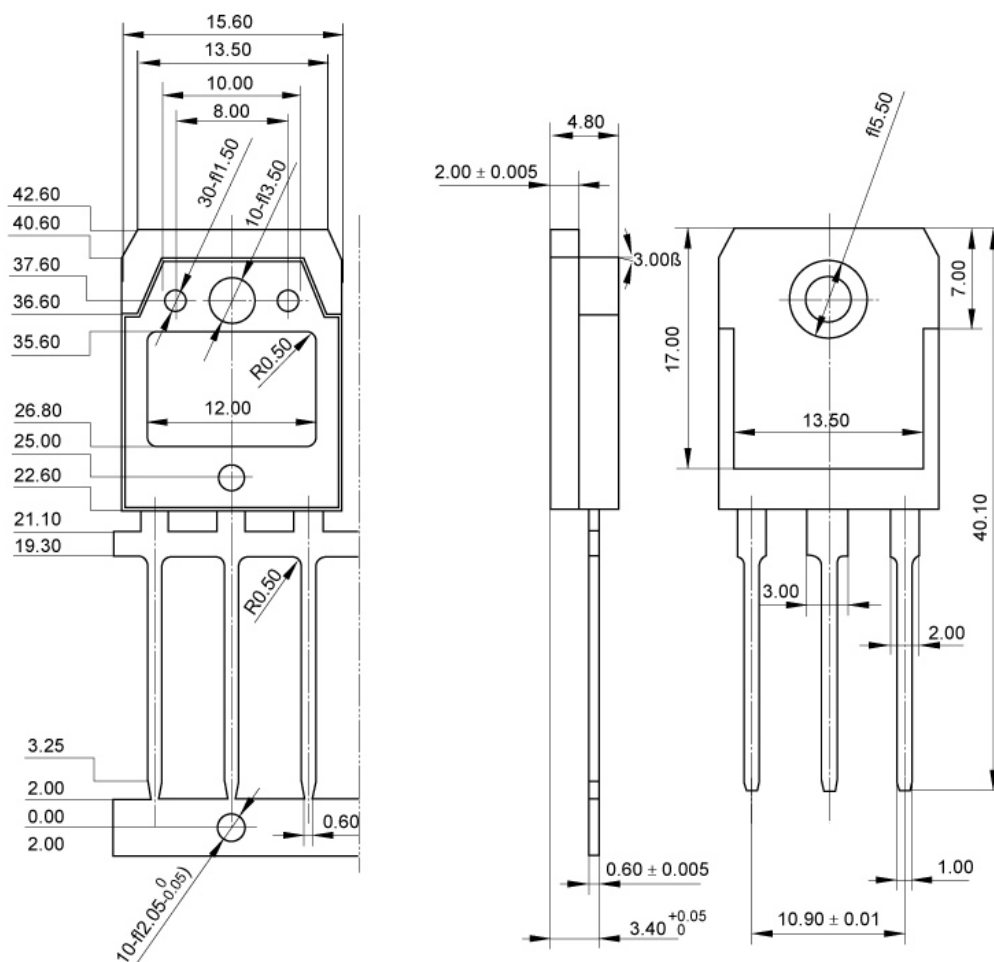
Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $R_{BE}=\infty$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA$; $I_E=0$	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=0.8A$; $V_{CE}=5V$	15		50	
h_{FE-2}	DC current gain	$I_C=4A$; $V_{CE}=5V$	10			

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)